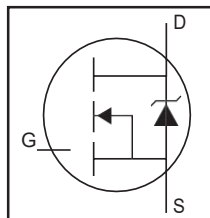


IRLB3036PbF

HEXFET® Power MOSFET

Applications

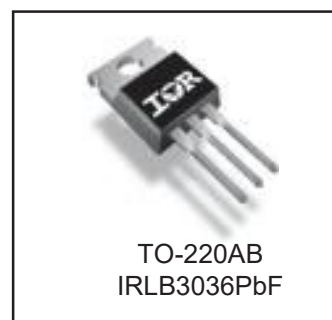
- DC Motor Drive
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits



V_{DS}	60V
$R_{DS(on)}$ typ.	1.9mΩ
max.	2.4mΩ
I_D (Silicon Limited)	270A
I_D (Package Limited)	195A

Benefits

- Optimized for Logic Level Drive
- Very Low $R_{DS(ON)}$ at 4.5V V_{GS}
- Superior R^*Q at 4.5V V_{GS}
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	270	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	190	
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Package Limited)	195	
I_{DM}	Pulsed Drain Current	1100	
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	380	W
	Linear Derating Factor	2.5	W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 16	V
dv/dt	Peak Diode Recovery	8.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	$^\circ\text{C}$
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb in (1.1N m)	

Avalanche Characteristics

E_{AS} (Thermally limited)	Single Pulse Avalanche Energy	290	mJ
I_{AR}	Avalanche Current	See Fig. 14, 15, 22a, 22b	A
E_{AR}	Repetitive Avalanche Energy		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.40	$^\circ\text{C/W}$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount)	—	62	

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.061	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 5mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.9	2.4	m Λ	$V_{GS} = 10V, I_D = 165A$
		—	2.2	2.8		$V_{GS} = 4.5V, I_D = 140A$
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 60V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 60V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
$R_{G(int)}$	Internal Gate Resistance	—	2.0	—	Λ	

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	340	—	—	S	$V_{DS} = 10V, I_D = 165A$
Q_g	Total Gate Charge	—	91	140	nC	$I_D = 165A$
Q_{gs}	Gate-to-Source Charge	—	31	—		$V_{DS} = 30V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	51	—		$V_{GS} = 4.5V$
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	40	—		$I_D = 165A, V_{DS} = 0V, V_{GS} = 4.5V$
$t_{d(on)}$	Turn-On Delay Time	—	66	—	ns	$V_{DD} = 39V$
t_r	Rise Time	—	220	—		$I_D = 165A$
$t_{d(off)}$	Turn-Off Delay Time	—	110	—		$R_G = 2.1\Lambda$
t_f	Fall Time	—	110	—		$V_{GS} = 4.5V$
C_{iss}	Input Capacitance	—	11210	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1020	—		$V_{DS} = 50V$
C_{rss}	Reverse Transfer Capacitance	—	500	—		$f = 1.0MHz$
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related)	—	1430	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 48V$
$C_{oss \text{ eff. (TR)}}$	Effective Output Capacitance (Time Related)	—	1880	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 48V$

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	270	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode)	—	—	1100		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 165A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	—	62	—	ns	$T_J = 25^\circ\text{C}$ $V_R = 51V,$
		—	66	—		$T_J = 125^\circ\text{C}$ $I_F = 165A$
Q_{rr}	Reverse Recovery Charge	—	310	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$
		—	360	—		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	4.4	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature Bond wire current limit is 195A. Note that current limitation arising from heating of the device leads may occur with some lead mounting arrangements.
Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.021mH$
 $R_G = 25\Lambda$, $I_{AS} = 165A$, $V_{GS} = 10V$. Part not recommended for use above this value.
- ④ $I_{SD} \leq 165A$, $di/dt \leq 430A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.

Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.

- ⑧ $C_{oss \text{ eff. (TR)}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note # AN-994 techniques refer to application note #AN-994.
- ⑨ R_{θ} is measured at T_J approximately 90°C .

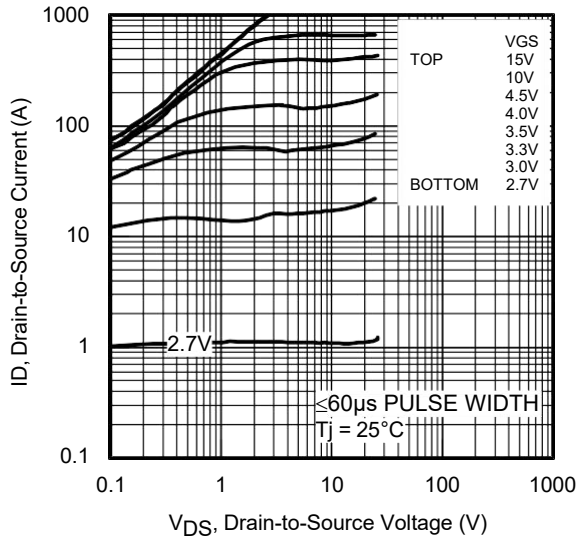


Fig 1. Typical Output Characteristics

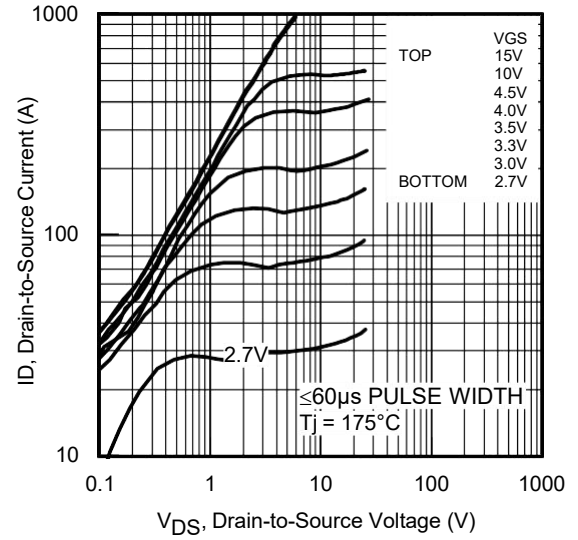


Fig 2. Typical Output Characteristics

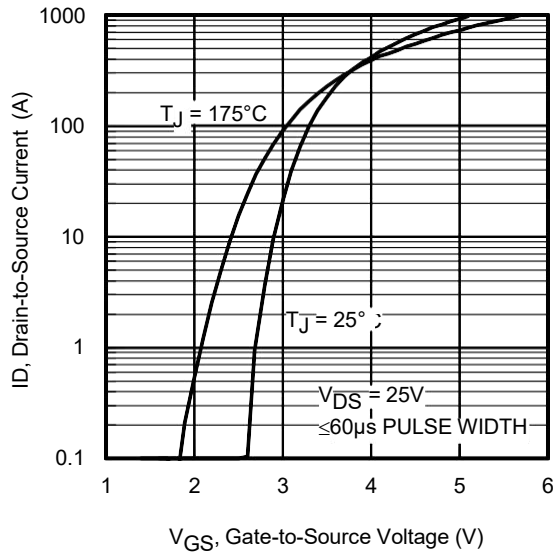


Fig 3. Typical Transfer Characteristics

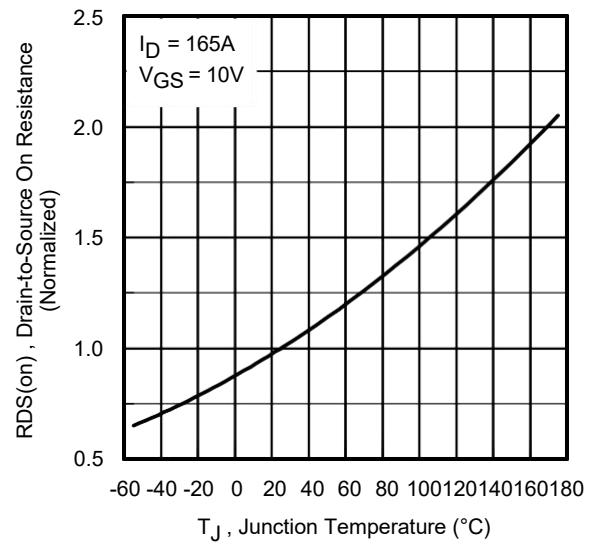


Fig 4. Normalized On-Resistance vs. Temperature

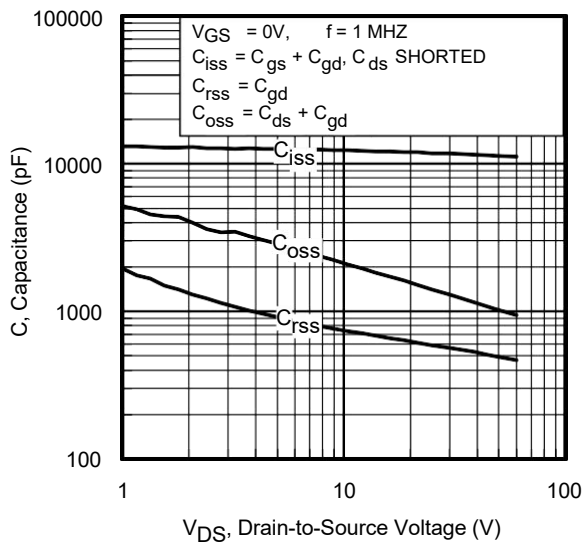


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

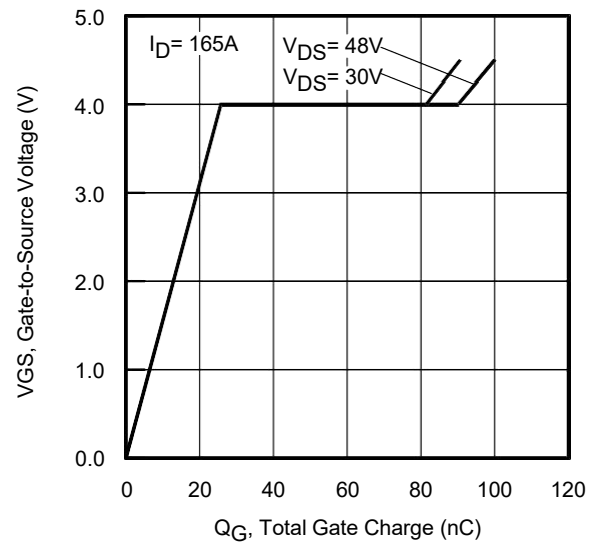


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

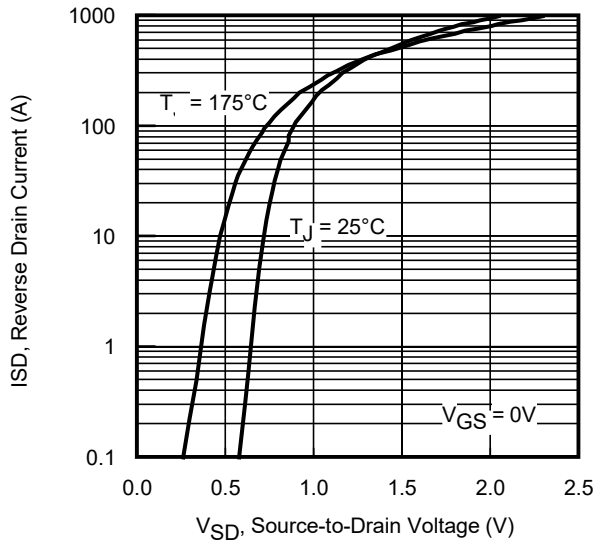


Fig 7. Typical Source-Drain Diode Forward Voltage

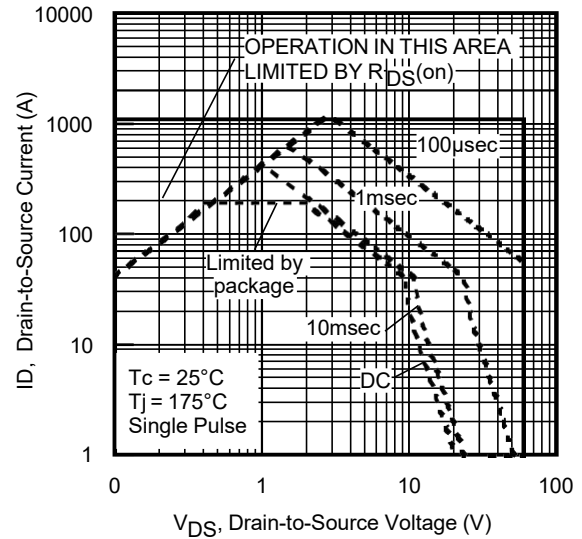


Fig 8. Maximum Safe Operating Area

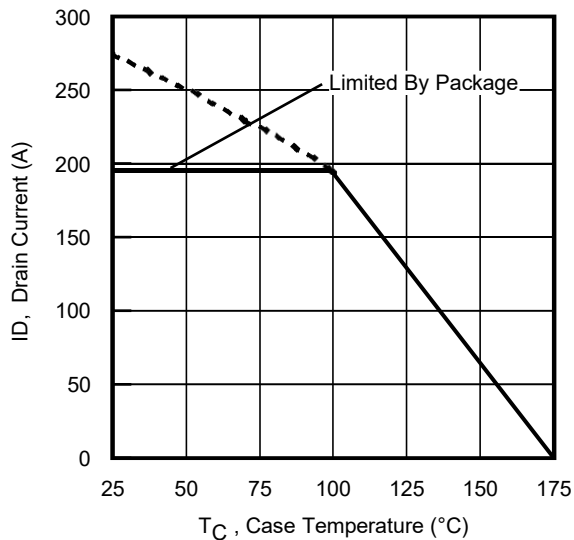


Fig 9. Maximum Drain Current vs. Case Temperature

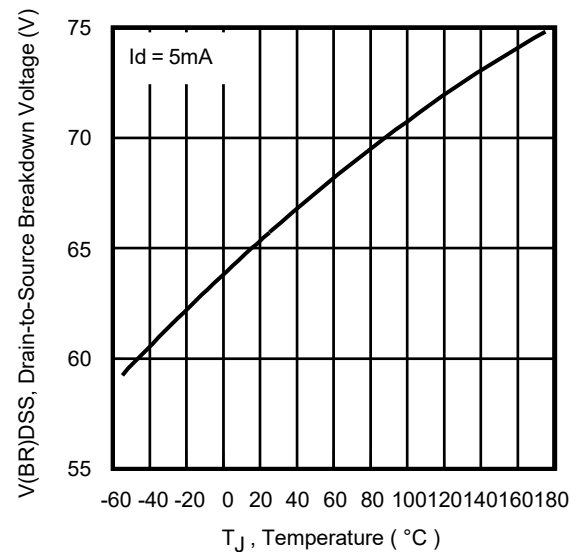


Fig 10. Drain-to-Source Breakdown Voltage

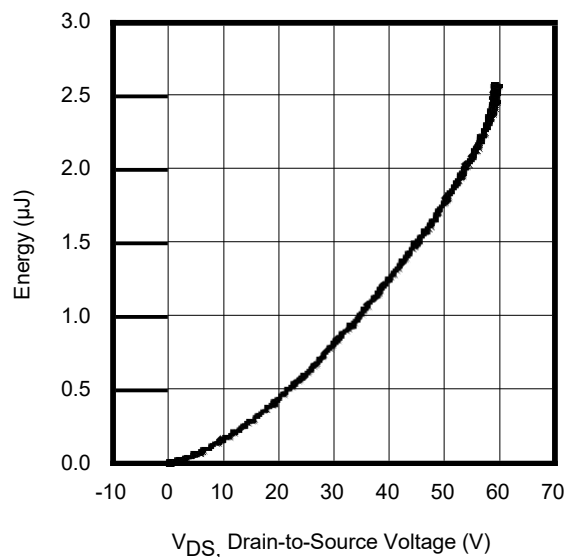


Fig 11. Typical C_{OSS} Stored Energy

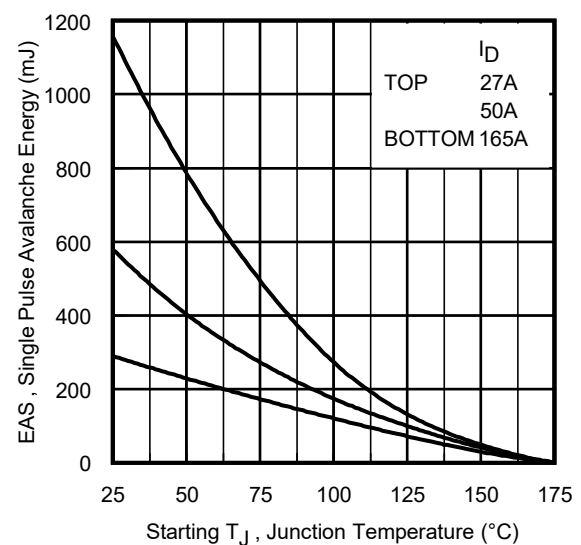


Fig 12. Maximum Avalanche Energy vs. Drain Current

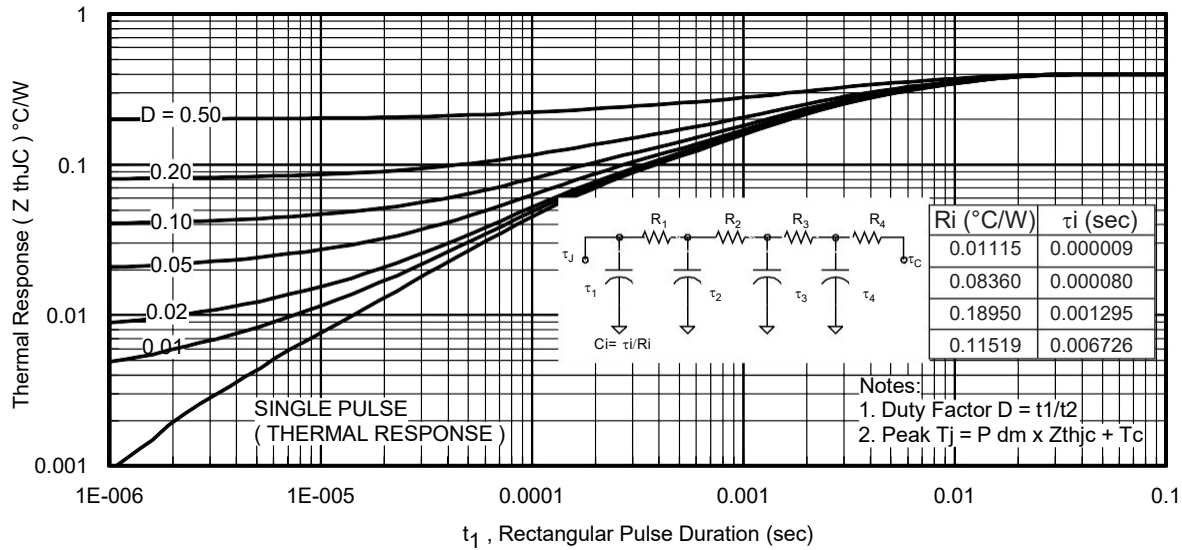


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

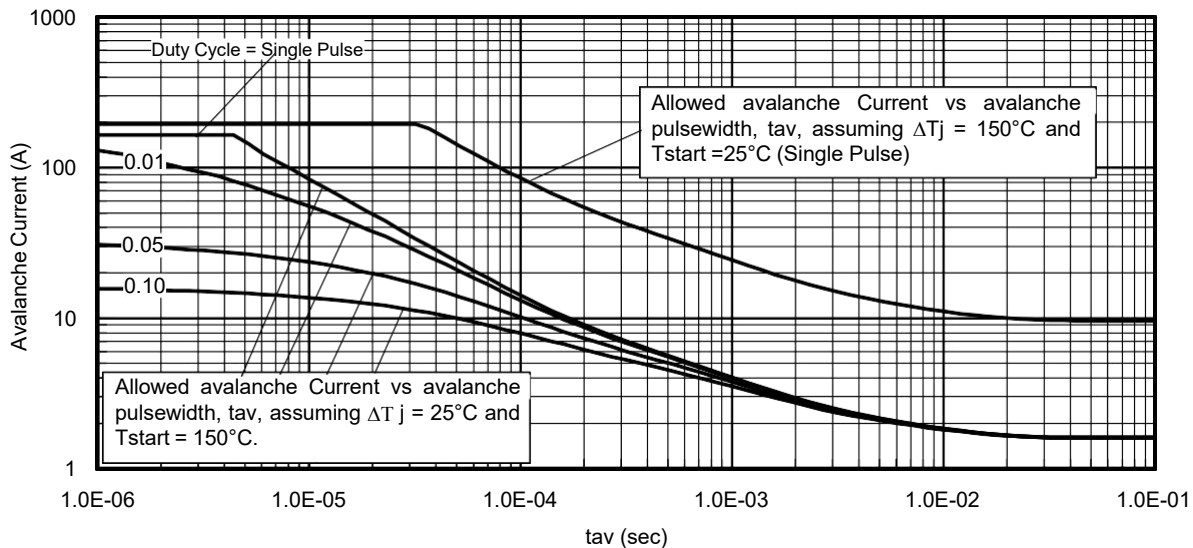


Fig 14. Typical Avalanche Current vs. Pulsewidth

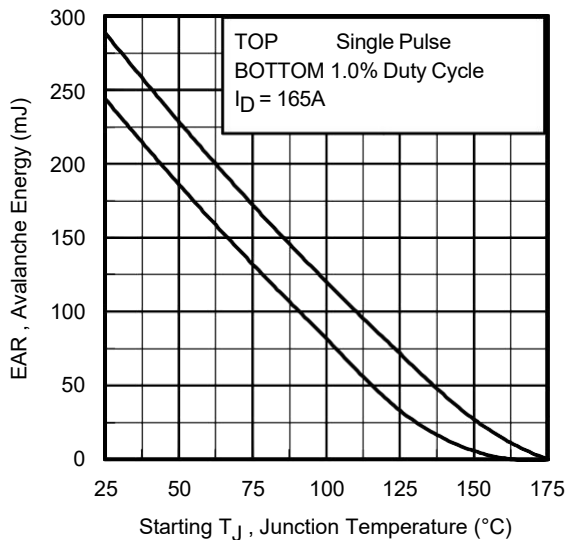


Fig 15. Maximum Avalanche Energy vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thjc}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thjc}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

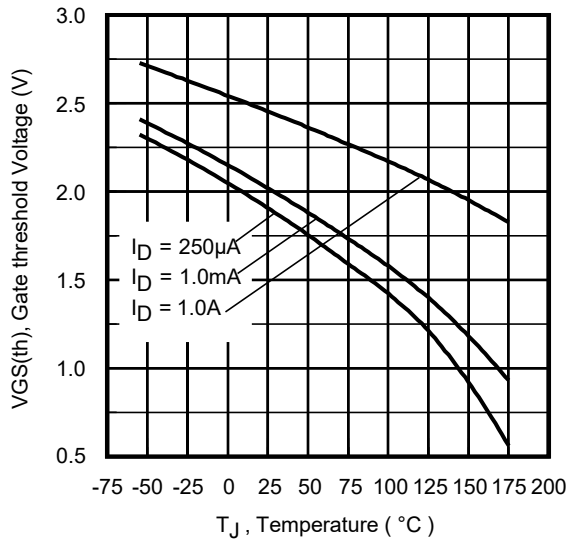
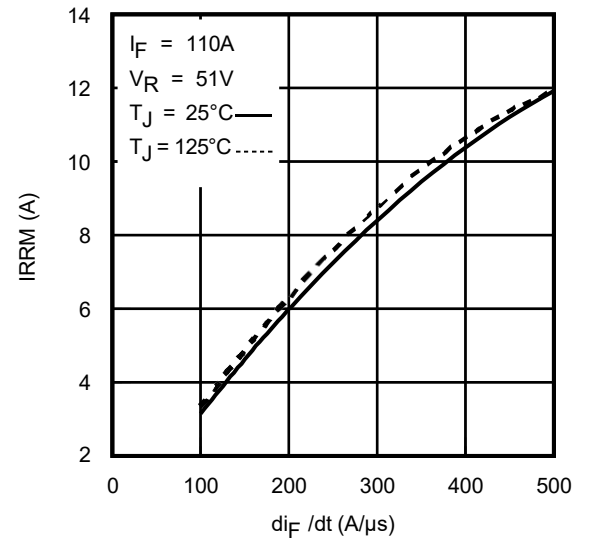
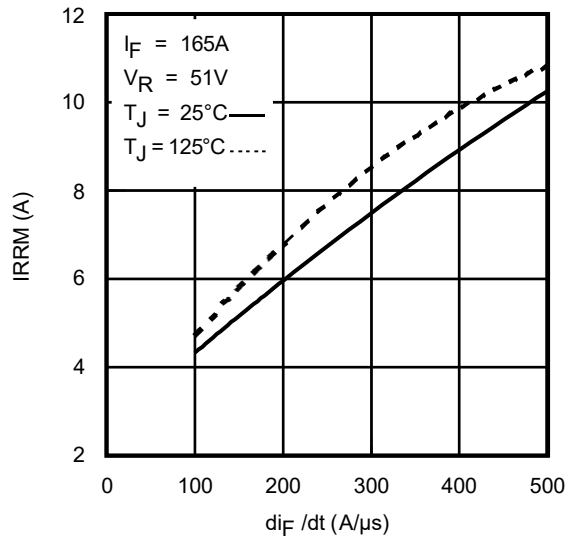
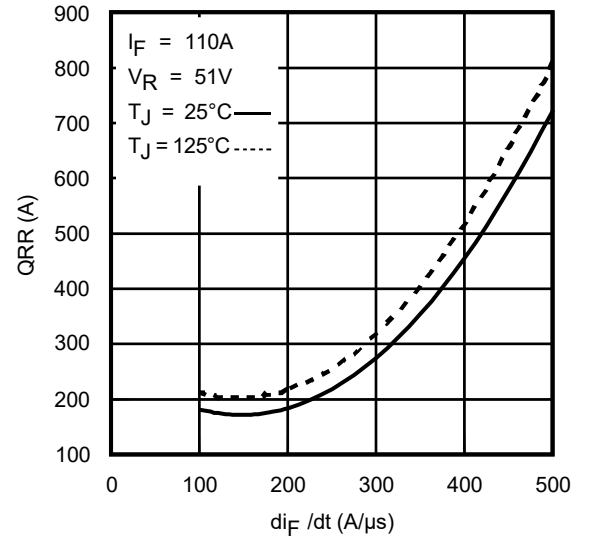
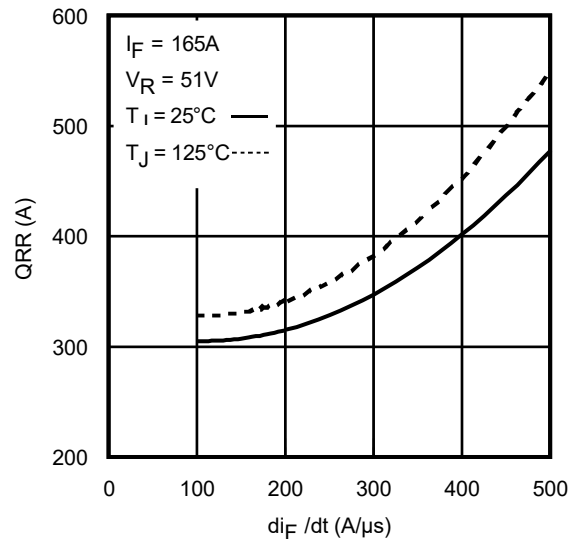


Fig. 16. Threshold Voltage vs. Temperature

Fig. 17 - Typical Recovery Current vs. di_T/dt Fig. 18 - Typical Recovery Current vs. di_T/dt Fig. 19 - Typical Stored Charge vs. di_T/dt Fig. 20 - Typical Stored Charge vs. di_T/dt

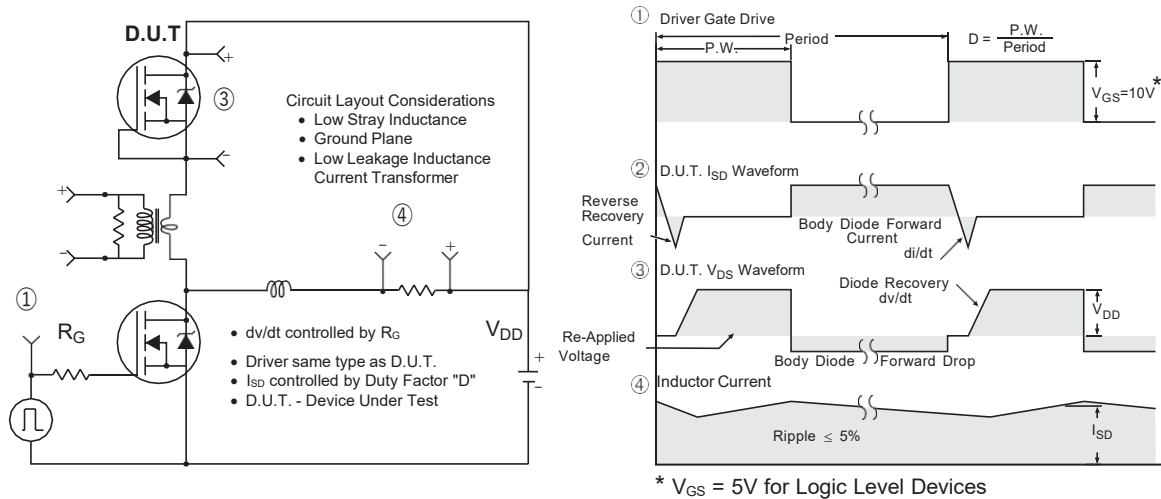


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

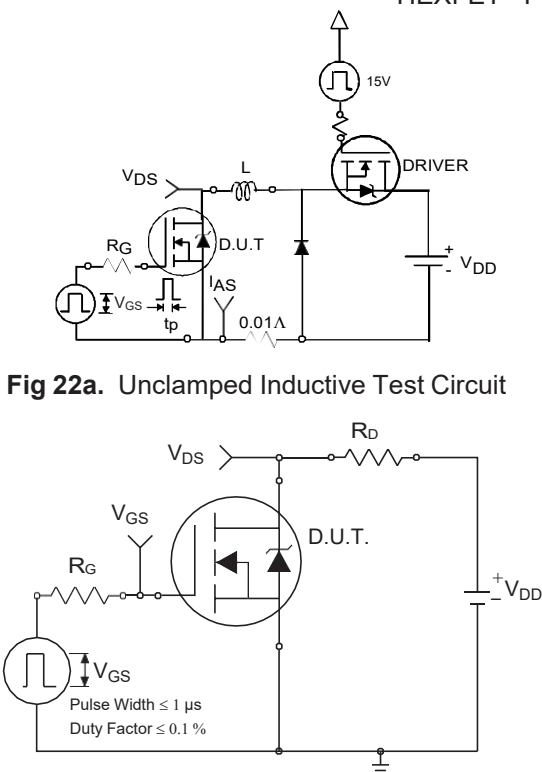


Fig 22a. Unclamped Inductive Test Circuit

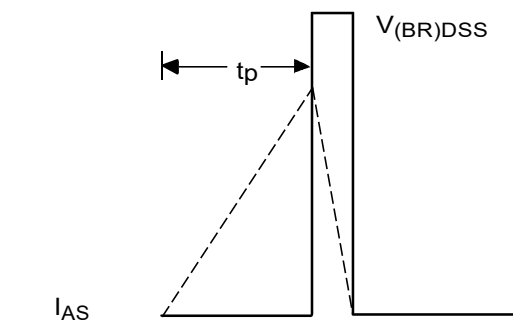


Fig 22b. Unclamped Inductive Waveforms

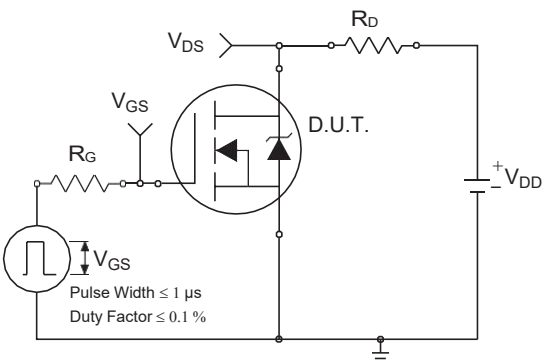


Fig 23a. Switching Time Test Circuit

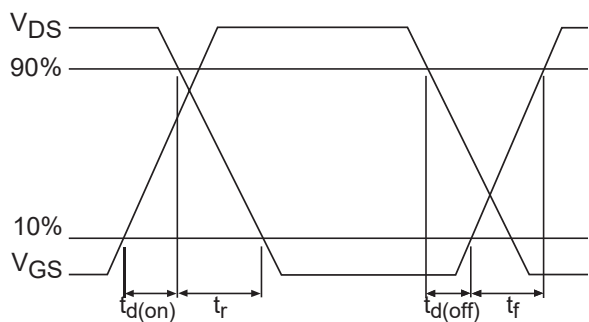


Fig 23b. Switching Time Waveforms

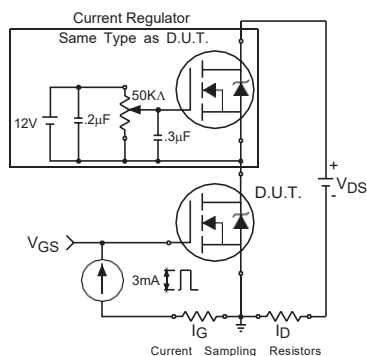


Fig 24a. Gate Charge Test Circuit

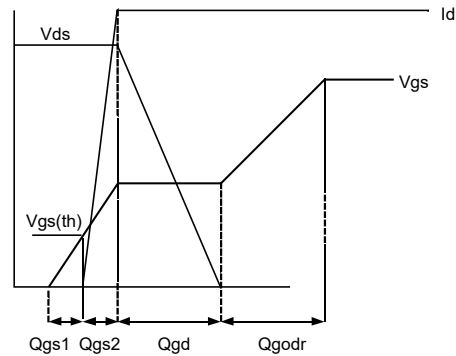
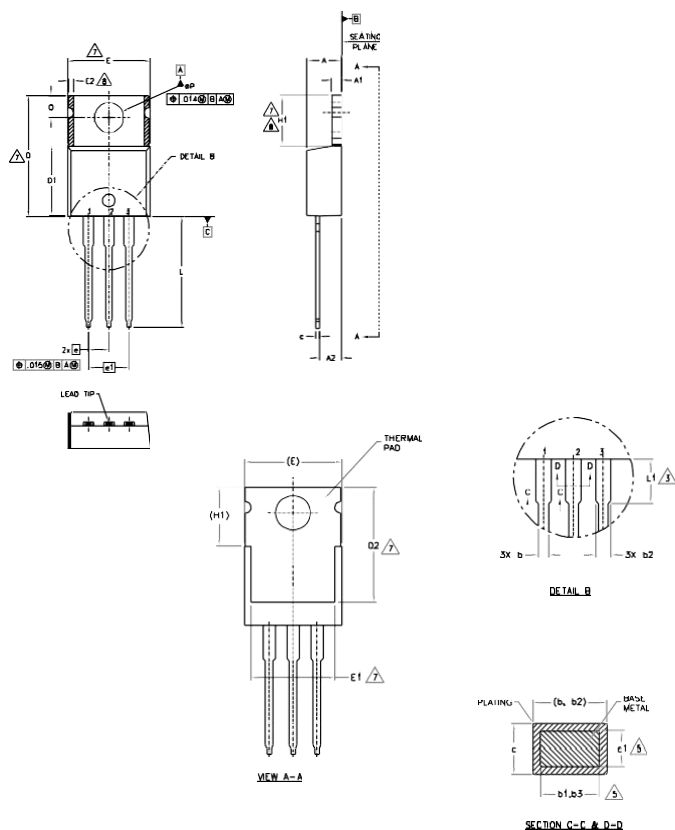


Fig 24b. Gate Charge Waveform

Dimensions are shown in millimeters (inches)



- 1- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
- 3- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 6- CONTROLLING DIMENSION - INCHES.
- 7- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

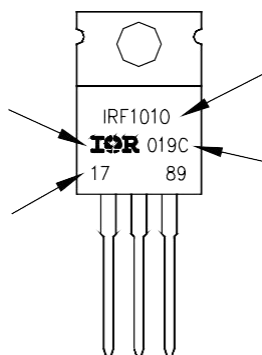
SYMBOL	DIMENSIONS				NOTES	
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	3.56	4.83	.140	.190	5	
A1	0.51	1.40	.020	.055		
A2	2.03	2.92	.080	.115		
b	0.38	1.01	.015	.040		
b1	0.38	0.97	.015	.038		
b2	1.14	1.78	.045	.070	5	
b3	1.14	1.73	.045	.068		
c	0.36	0.61	.014	.024		
c1	0.36	0.56	.014	.022		
D	14.22	16.51	.560	.650		4
D1	8.38	9.02	.330	.355	7	
D2	11.68	12.88	.460	.507		
E	9.65	10.67	.380	.420		4,7
E1	6.86	8.89	.270	.350		7
E2	-	0.76	-	.030		8
e	2.54 BSC		.100 BSC		7,8	
e1	5.08 BSC		.200 BSC			
H1	5.84	6.86	.230	.270	3	
L	12.70	14.73	.500	.580		
L1	3.56	4.06	.140	.160		
ØP	3.54	4.08	.139	.161		
Q	2.54	3.42	.100	.135		

1.- GATE
2.- COLLECTOR
3.- EMITTER

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>



Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International IOR Rectifier

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TAC Fax: (310) 252-7903

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